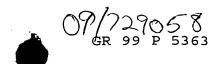
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Abstract of the Disclosure:

The capacitive electrode structure has a semiconductor substrate, a metal oxide layer on the semiconductor substrate, an oxidation inhibiting layer on the metal oxide layer, and an electrode formed on the oxidation inhibiting layer. The oxidation inhibiting layer is substantially impervious to oxygen and prevents oxygen atoms from diffusing into the metal oxide layer.

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